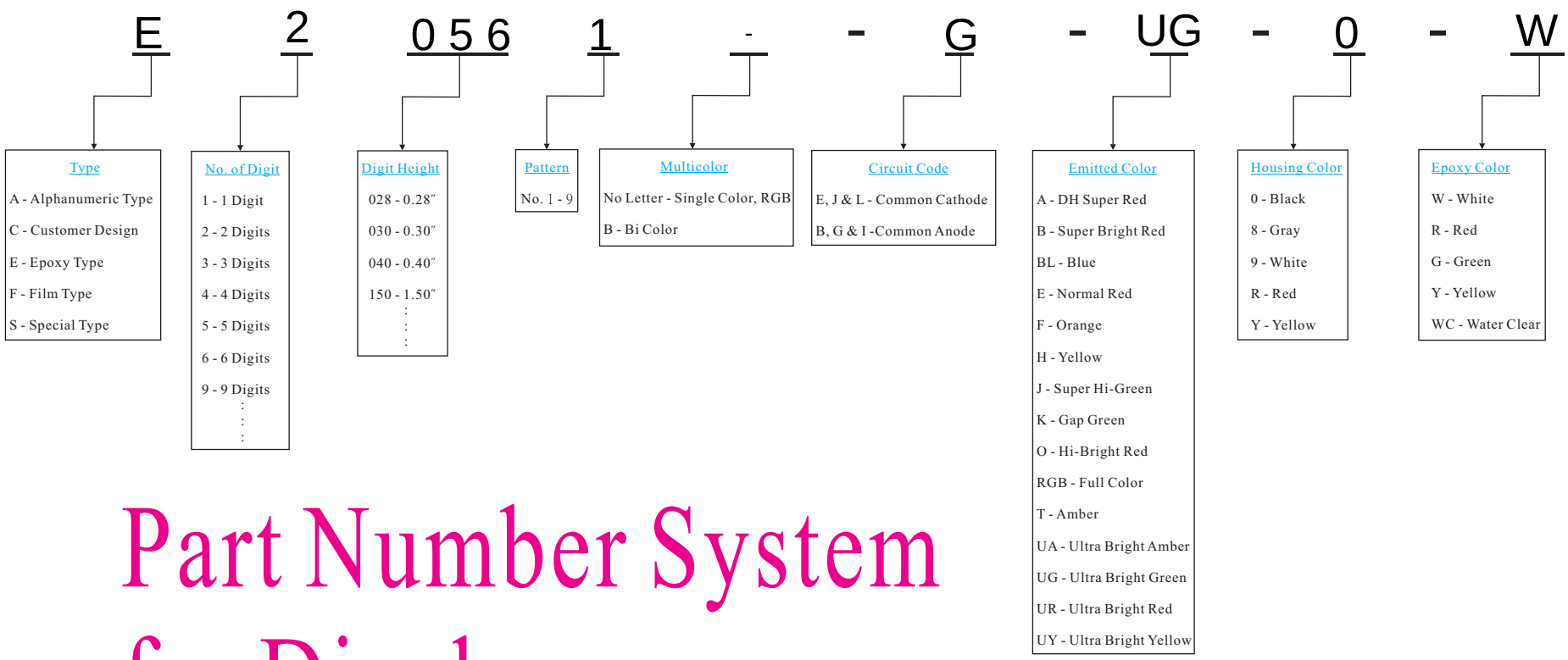
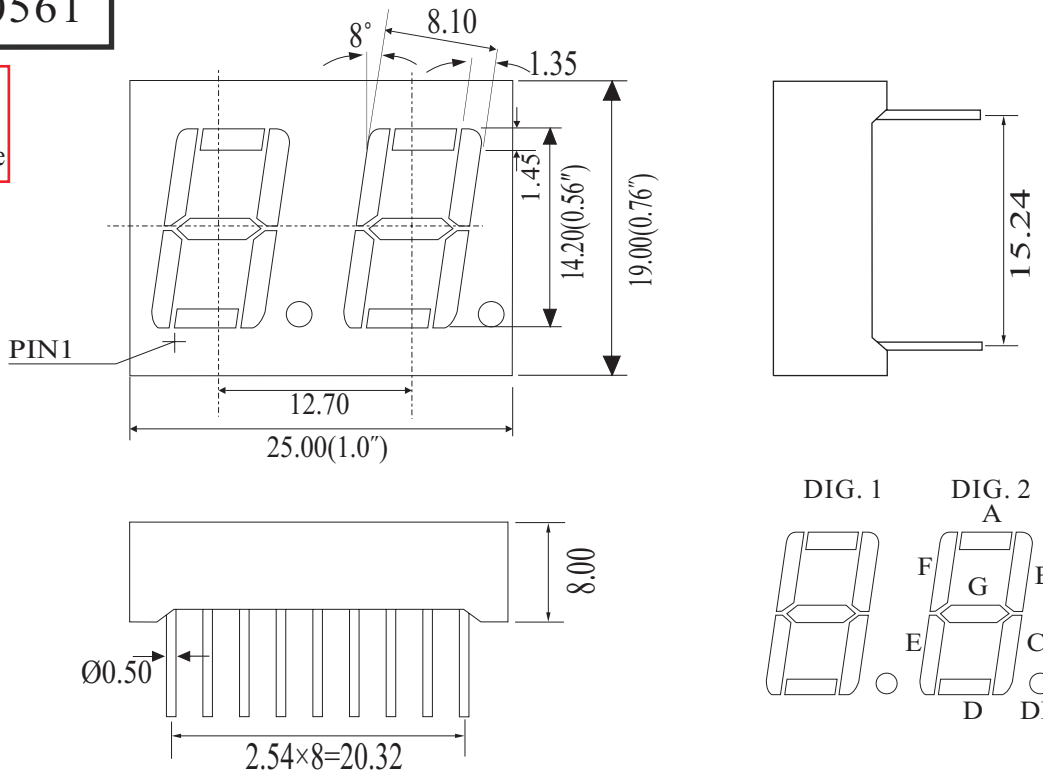


Part Number System for Displays

PACKAGE DIMENSION

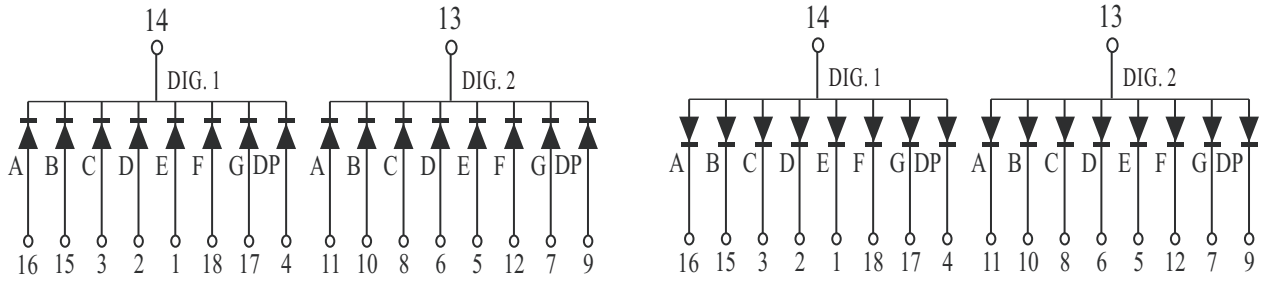
E20561

Pb
Pb-free



UNIT: MM(INCH) TOLERANCE: ±0.25(0.01")

INTERNAL CIRCUIT DIAGRAM



CODE J

CODE G

CODE UG

Chip Material: AlGaInP / GaAs Yellow Green LED Chip

Pb-free

ABSOLUTE MAXIMUM RATINGS (Ta = 25℃)

PARAMETER	SYMBOL	MAXIMUM RATING	UNIT
Power Dissipation	P_D	62	mW
Peak Forward Current (1/10 Duty Cycle, 0.1 Ms Pulse Width)	I_{PEAK}	140	mA
DC Forward Current	I_F	25	mA
Reverse Voltage	V_R	5	V
Operating Temperature Range	T_A	-40°C to +85°C	
Storage Temperature Range	T_{STG}	-40°C to +85°C	
Solder temperature 1/16 inch below seating plane for 3 seconds at 260°C			

ELECTRICAL OPTICAL CHARACTER AND CURVES (Ta = 25℃)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	LOCATION	TEST CONDITION
Forward Voltage	V_F	-	2.20	2.50	V	Per Chip	I_F =20mA
Luminous Intensity	I_V	40.0	45.0	50.0	mcd	Per Chip	I_F =20mA
Peak Emission Wavelength	λp	-	575	-	nm	Per Chip	I_F =20mA
Dominant Emission Wavelength	λd	567	572	577	nm	Per Chip	I_F =20mA
Spectral Line Half-Width	Δλ1/2	-	20	-	nm	Per Chip	I_F =20mA
Capacitance	C	-	15	-	pF	Per Chip	VF=0V;f=1MHz
Reverse Current	I_R	-	-	10	uA	Per Chip	VR = 5V

Note:

1. **Luminous intensity tolerance is ±10%;**
2. **Dominant Emission Wavelength tolerance is ±5%.**

CODE UG

■ Typical Electro-Optical Characteristic Curve:

FIG. 1 Forward Current Vs. Forward Voltage

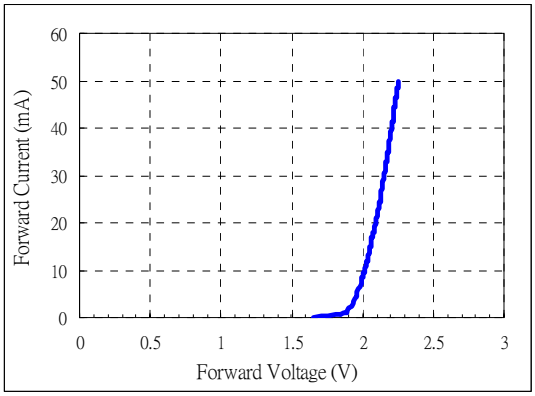


FIG. 2 Relative Intensity Vs. Forward Current

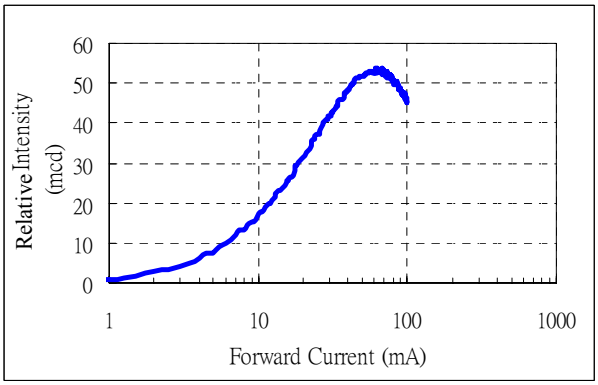


FIG. 3 Forward Voltage Vs. Temperature

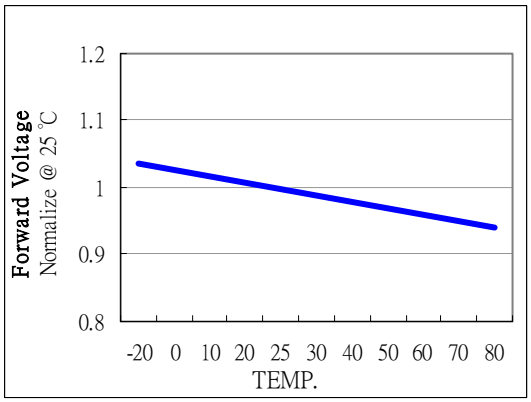


FIG. 4 Relative Intensity Vs. Temperature

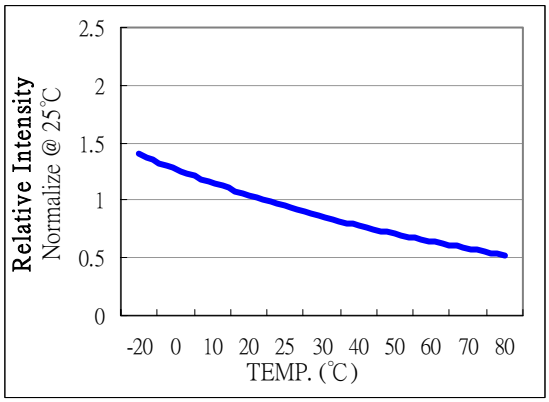


FIG. 5 Relative Intensity Vs. Wavelength